

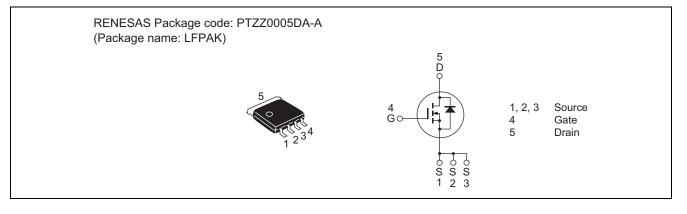
100V, 25A, 14m $\Omega$  max. Silicon N Channel Power MOS FET Power Switching

R07DS1059EJ0200 (Previous: REJ03G1888-0100) Rev.2.00 Apr 11, 2013

# Features

- High speed switching
- Low drive current
- Low on-resistance
  - $R_{DS(on)} = 11 \text{ m}\Omega \text{ typ.}$  (at  $V_{GS} = 10 \text{ V}$ )
- Pb-free
- Halogen-free
- High density mounting

### Outline



# **Absolute Maximum Ratings**

|  |                             |             | $(1a = 25^{\circ}C)$ |
|--|-----------------------------|-------------|----------------------|
| Item                                   | Symbol                      | Ratings     | Unit                 |
| Drain to source voltage                | V <sub>DSS</sub>            | 100         | V                    |
| Gate to source voltage                 | V <sub>GSS</sub>            | ±20         | V                    |
| Drain current                          | I <sub>D</sub>              | 25          | A                    |
| Drain peak current                     | I <sub>D(pulse)</sub> Note1 | 100         | A                    |
| Body-drain diode reverse drain current | I <sub>DR</sub>             | 25          | A                    |
| Avalanche current                      | I <sub>AP</sub> Note 2      | 25          | A                    |
| Avalanche energy                       | E <sub>AS</sub> Note 2      | 6.3         | mJ                   |
| Channel dissipation                    | Pch Note3                   | 65          | W                    |
| Channel to Case Thermal Resistance     | θch-C                       | 1.92        | °C/W                 |
| Channel temperature                    | Tch                         | 150         | °C                   |
| Storage temperature                    | Tstg                        | -55 to +150 | °C                   |

Notes: 1.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

2. Value at L=10uH, Tch = 25°C, Rg  $\geq$  50  $\Omega$ 

3. Tc = 25°C



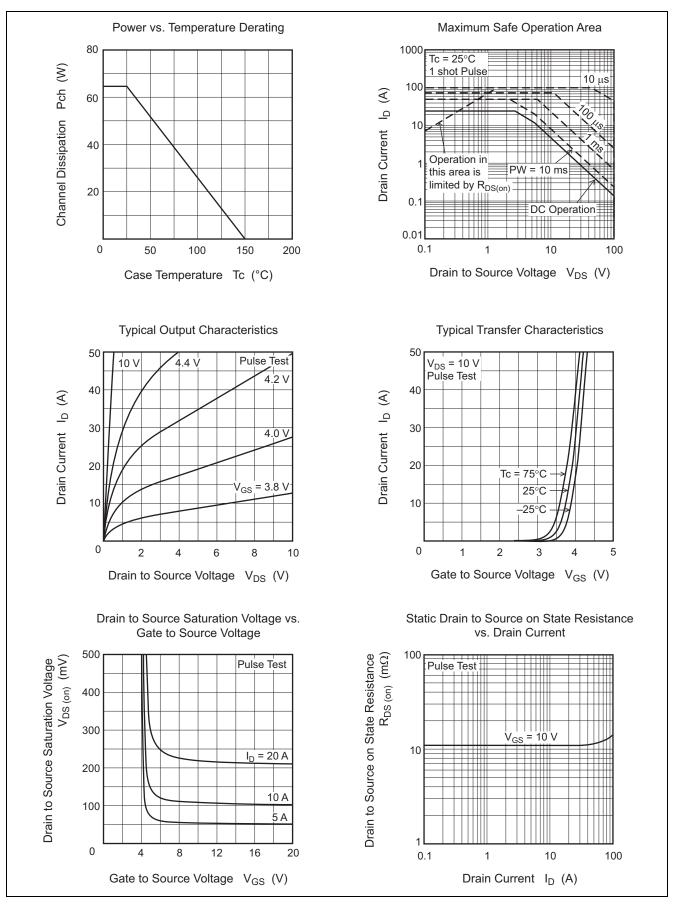
# **Electrical Characteristics**

|  |                      |     |      |      |      | $(Ta = 25^{\circ}C)$  |
|--|----------------------|-----|------|------|------|---|
| Item                                       | Symbol               | Min | Тур  | Max  | Unit | Test Conditions   |
| Drain to source breakdown voltage          | V <sub>(BR)DSS</sub> | 100 |      | —    | V    | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$   |
| Gate to source leak current                | I <sub>GSS</sub>     | _   |      | ±0.1 | μΑ   | $V_{GS} = \pm 20 \text{ V},  V_{DS} = 0 \text{ V}$  |
| Zero gate voltage drain current            | I <sub>DSS</sub>     | _   |      | 1    | μΑ   | $V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$  |
| Gate to source cutoff voltage              | V <sub>GS(off)</sub> | 2.0 |      | 4.0  | V    | $V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$   |
| Static drain to source on state resistance | R <sub>DS(on)</sub>  | _   | 11   | 14   | mΩ   | $I_D = 12.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$   |
| Forward transfer admittance                | y <sub>fs</sub>      | _   | 42   | —    | S    | $I_D = 12.5 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$   |
| Input capacitance                          | Ciss                 | _   | 3000 | _    | pF   | $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$  |
| Output capacitance                         | Coss                 | _   | 490  | _    | pF   | f = 1 MHz   |
| Reverse transfer capacitance               | Crss                 | _   | 120  | _    | pF   |   |
| Gate Resistance                            | Rg                   | _   | 0.5  | _    | Ω    |   |
| Total gate charge                          | Qg                   | _   | 41   | —    | nC   | $V_{DD} = 50 \text{ V}, \text{ V}_{GS} = 10 \text{ V},$   |
| Gate to source charge                      | Qgs                  | _   | 13   | —    | nC   | I <sub>D</sub> = 25 A   |
| Gate to drain charge                       | Qgd                  | _   | 7.5  | _    | nC   |   |
| Turn-on delay time                         | t <sub>d(on)</sub>   | _   | 16   | _    | ns   | $V_{GS} = 10 \text{ V}, I_D = 12.5 \text{ A},$  |
| Rise time                                  | tr                   | _   | 4.5  | _    | ns   | $\label{eq:VDD} \begin{array}{l} V_{DD} \cong 30 \ V, \ R_{L} = 2.4 \ \Omega, \\ Rg = 4.7 \ \Omega \end{array}$ |
| Turn-off delay time                        | t <sub>d(off)</sub>  | _   | 36   |      | ns   |   |
| Fall time                                  | t <sub>f</sub>       | _   | 6.5  |      | ns   |   |
| Body-drain diode forward voltage           | V <sub>DF</sub>      | _   | 0.8  | 1.1  | V    | $I_F = 25 \text{ A}, V_{GS} = 0 \text{ V}^{Note4}$  |
| Body-drain diode reverse recovery time     | t <sub>rr</sub>      |     | 52   |      | ns   | $I_F = 25 \text{ A}, V_{GS} = 0 \text{ V}$  |
|  |                      |     |      |      |      | di <sub>F</sub> / dt = 100 A/ μs  |

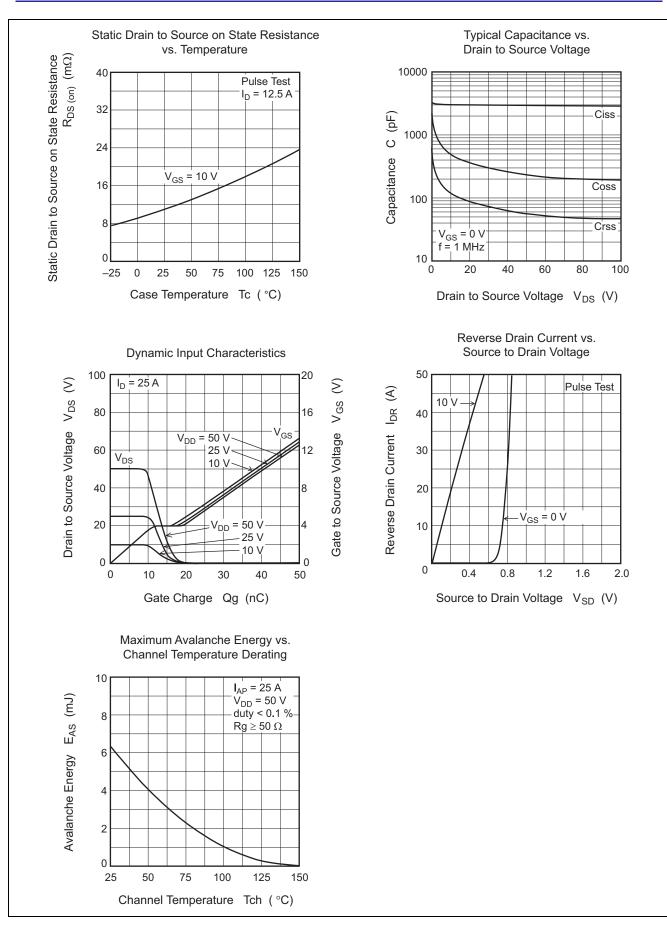
Notes: 4. Pulse test

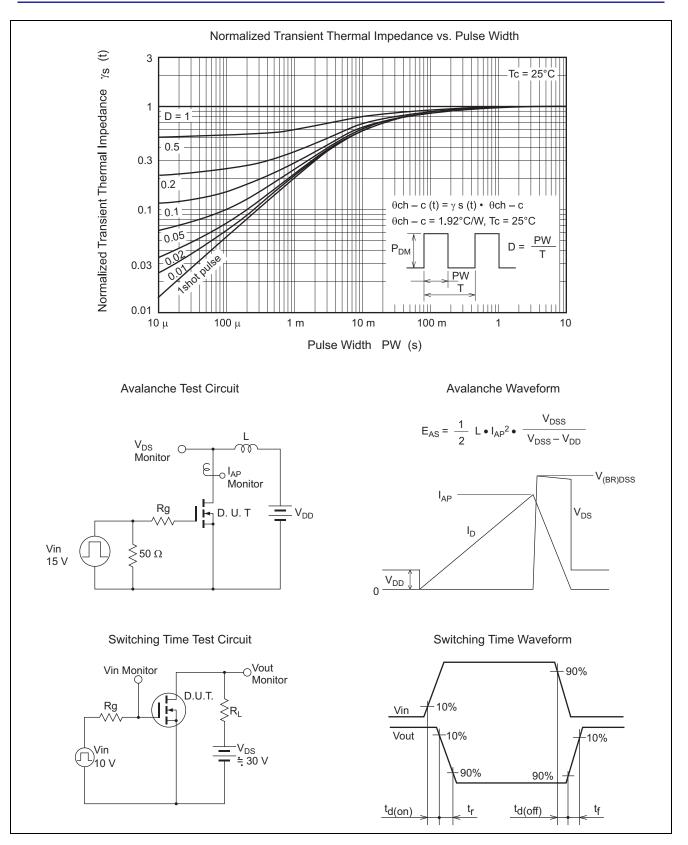


# **Main Characteristics**



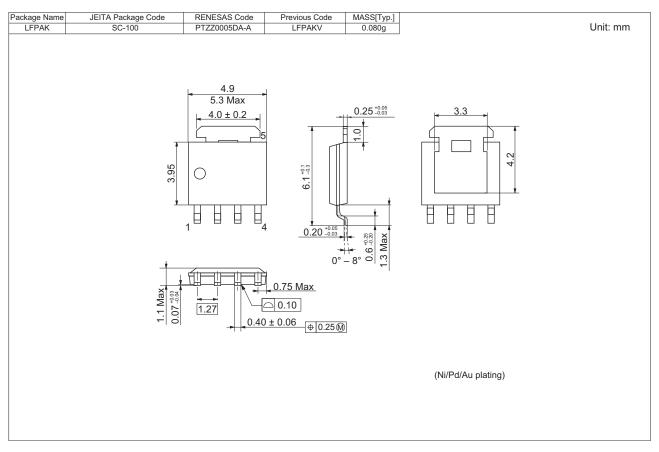








# **Package Dimensions**



# **Ordering Information**

| Part No.         | Quantity | Shipping Container |
|------------------|----------|--------------------|
| RJK1056DPB-00-J5 | 2500 pcs | Taping             |



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